Silicon NPN transistor in a TO-252 Plastic Package.

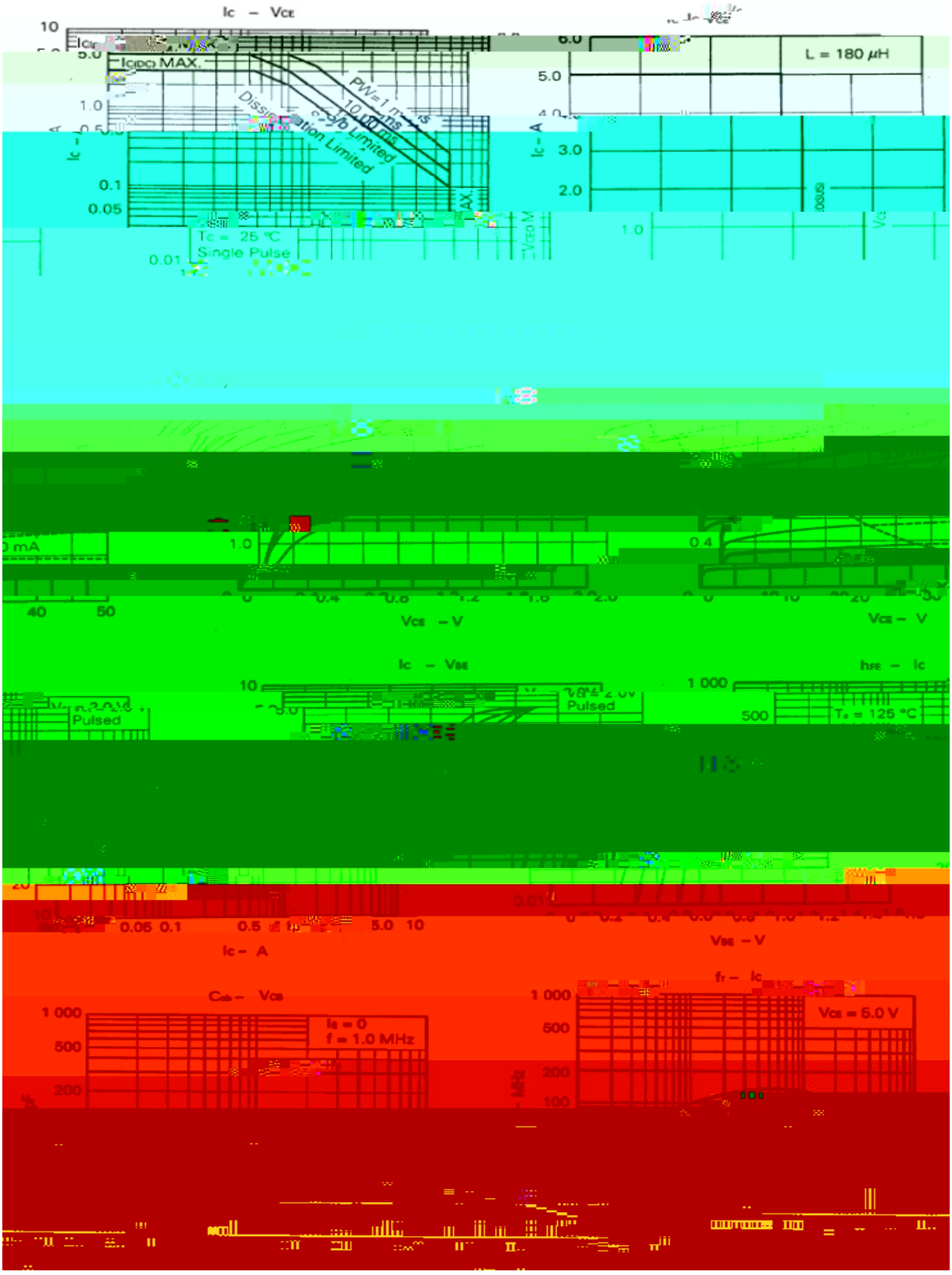
Low $V_{CE(sat)}$, 10.5 62.94 731.2403 Tm-0.0002 Tc[303a47.3602203 Tm-0.0009 T2dirent and 009 Tf0.5 6(at)-5.1())]TJ2T

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	3.0	A
Collector Power Dissipation*	*P_C	2.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

*When mounted on a 7.5×7.5×0.7mm ceramic board

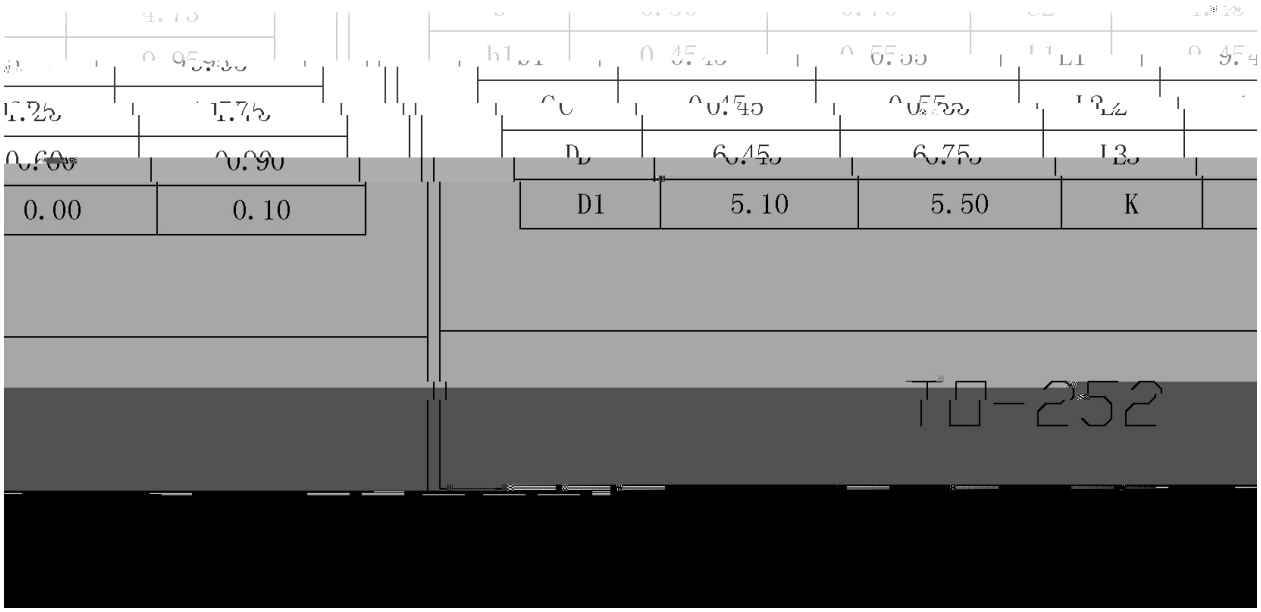
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=100μA I_E=0	60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	60			V

/ Electrical Characteristic Curve

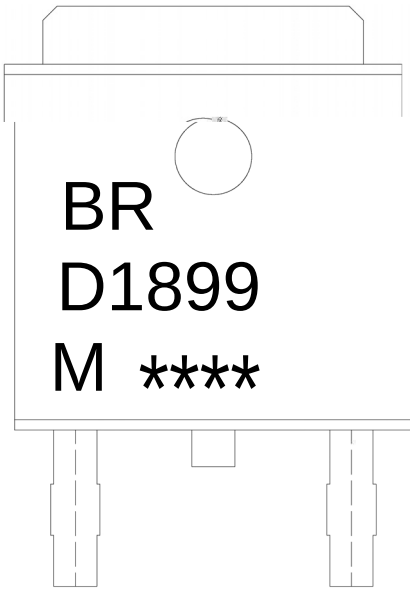


/ Package Dimensions





/ Marking Instructions



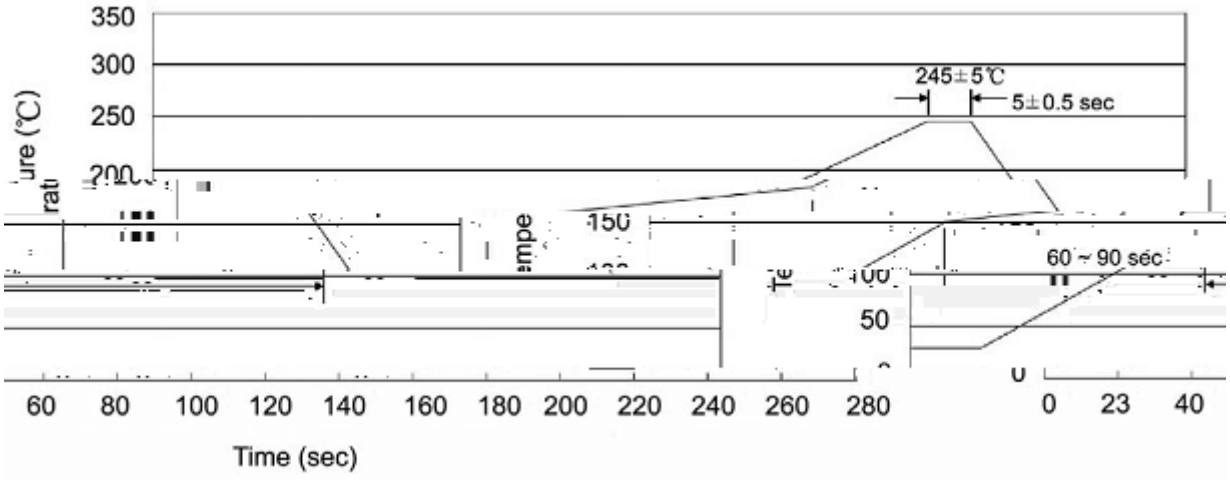
BR

h_{FE}

Note:

BR:	Company Code
D1899:	Product Type.
M:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1 25 150 60 90sec;

1.Preheating:25~150 , Time:60~90sec.

2 245 5 5 0.5sec;

2.Peak Temp.:245 5 , Duration:5 0.5sec.

3 2 10 /sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension		(unit mm^3)
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
TO-252	2,500	2	5,000	5	25,000	13 ×16	360×360×50	385×257×392

/ TUBE

Package Type	Units					Dimension		(unit mm^3)
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180